

# InGaAs Avalanche Photodiode (APD) with Integrated Lens 10 Gbps (Chip-on-Carrier)

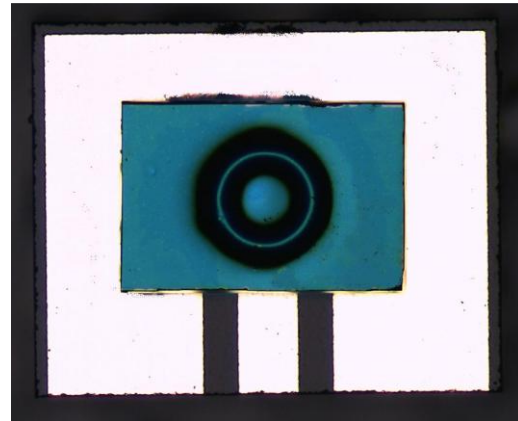
PDAB0022L-CC

## Applications

Long Haul Receivers  
SONET/SDH Receivers

## Features

Ceramic sub-carrier  
Integrated Lens  
Planer Structure for High Reliability  
1000 to 1625nm Spectral Response  
Low Dark Current



## Description

Go!Foton Avalanche Photodiode (APD) is suitable for 10 Gbps applications in optical communications. This InGaAs APD has a planer structure for high reliability. It has back illuminated structure. The optical signal goes through the integrated lens on the back surface.

## Specifications

### Electro-Optical Characteristics

Parameter	Min	Typ	Max	Conditions
Active Area Diameter ( $\mu\text{m}$ )		22		
Responsivity (A/W)	0.80			1.55 $\mu\text{m}$ , M=1
Dark Current (nA)			50	0.9V <sub>br</sub> , 25 °C
Breakdown Voltage (V)	25		40	100 $\mu\text{A}$
Capacitance (pF)			0.3	1MHz, M=10
Frequency Response (GHz)	7			M=8, RL=50 $\Omega$
Operating Voltage (V)			V <sub>br</sub> - 1	M=10
Punch-through Voltage (V)	12		V <sub>br</sub> - 7	
Temperature Coefficient of V <sub>b</sub> (%/°C)			0.15	

- 1) Condition unless noted: 25°C, P<sub>out</sub> = 1uW
- 2) Punch-through voltage is defined as voltage where 1.5V above the voltage where the first deviation of IV curve under illumination shows local maximum
- 3) Responsivity at punch-through voltage is defined as responsivity at M=1



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## Absolute Maximum Rating

Parameter	Min	Typ	Max
Reverse Current (mA)			1
Forward Current (mA)			1
Maximum Input Power (mW)			0.5
Operating Temperature <sup>4)</sup> (°C)	-40		85
Storage Temperature <sup>4)</sup> (°C)	-40		85

4) Operational or storage beyond these absolute maximum ratings causes permanent damage to the device.

## Drawing

